

24. (Withdrawn) A method of manufacturing a pyrolytic boron nitride double container for a source of molecular beams used in molecular beam epitaxy, comprising:

depositing pyrolytic boron nitride on a graphite mandrel by a CVD reaction, thereby forming the double container,

forming a doped layer in the pyrolytic boron nitride container by introducing a dopant gas during the CVD reaction of the inner container,

adjusting at least one of the thickness, area and the doping density of the doped layer,

setting the inner container transmissivity with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1} to 90% or less of an outer container transmissivity, with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1} , and

separating the double container from the mandrel.

25. (Previously Presented) The pyrolytic boron nitride double container according to claim 1, wherein said inner container transmissivity is 70% or less of said outer container transmissivity.

26. (Previously Presented) The pyrolytic boron nitride double container according to claim 1, wherein said inner container comprises pyrolytic boron nitride combined with another material.

27. (Previously Presented) The pyrolytic boron nitride double container according to claim 1, wherein said inner container comprises pyrolytic boron nitride combined with pyrolytic graphite.